

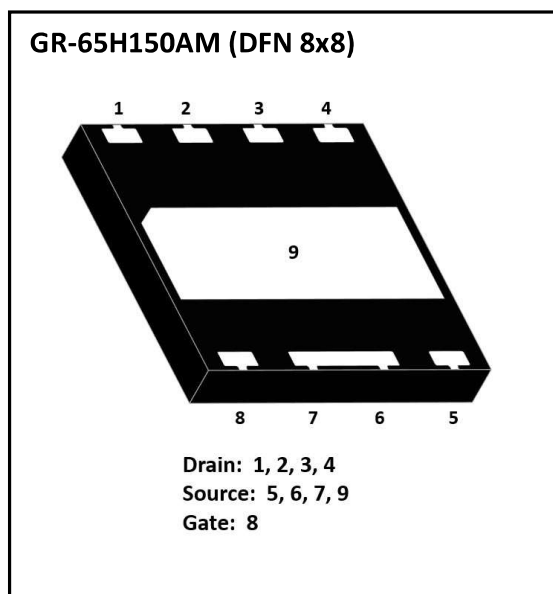
GR-65H150AM: DFN 8x8 HS E-mode GaN

Description

GR-65H150AM is an integrated GaN based power transistor which possesses not only enhancement mode (e-mode) GaN’s benefits but also compatibility with commonly-seen e-mode / Cascode GaN based power transistor and Si MOSFET. GR-65H150AD provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

Key Specifications

Part Number	GR-65H150AM
V_{DSS}	650V
$V_{(TR)DSS}$	800V
$R_{DS(ON)}$, typ.	150mΩ
Q_G , typ.	3nC
Package	DFN 8 x 8 mm



Features

- Gate drive voltage compatibility (-10V to 18V)
- High operating frequency
- Zero reverse recovery loss

Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/ DC-DC Converters
- Motor Drives

